

74HC2G00; 74HCT2G00

Dual 2-input NAND gate

Rev. 04 — 3 July 2008

Product data sheet

1. General description

The 74HC2G00 and 74HCT2G00 are high-speed Si-gate CMOS devices. They provide two 2-input NAND gates.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G00DP 74HCT2G00DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC2G00DC 74HCT2G00DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HC2G00GD 74HCT2G00GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2



4. Marking

Table 2. Marking code

Type number	Marking code
74HC2G00DP	H00
74HCT2G00DP	T00
74HC2G00DC	H00
74HCT2G00DC	T00
74HC2G00GD	H00
74HCT2G00GD	T00

5. Functional diagram

Fig 1. Logic symbol

Fig 2. IEC logic symbol

Fig 3. Logic diagram (one driver)

6. Pinning information

6.1 Pinning

Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

Fig 5. Pin configuration SOT996-2 (XSON8U)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	[1] -	±20	mA
I _O	output current	V _O = -0.5 V to (V _{CC} + 0.5 V)	[1] -	25	mA
I _{CC}	supply current		[1] -	50	mA
I _{GND}	ground current		[1] -50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _D	dynamic power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
 For XSON8 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC2G00			74HCT2G00			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ °C}$.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HC2G00								
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0\text{ V}$	1.5	1.2	-	1.5	-	V
		$V_{CC} = 4.5\text{ V}$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0\text{ V}$	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0\text{ V}$	-	0.8	0.5	-	0.5	V
		$V_{CC} = 4.5\text{ V}$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0\text{ V}$	-	2.8	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 2.0\text{ V}$	1.9	2.0	-	1.9	-	V
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	V
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 6.0\text{ V}$	5.9	6.0	-	5.9	-	V
		$I_O = -4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	4.13	4.32	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 2.0\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 6.0\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	0.15	0.33	-	0.4	V
		$I_O = 5.2\text{ mA}$; $V_{CC} = 6.0\text{ V}$	-	0.16	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0\text{ V}$	-	-	± 1.0	-	± 1.0	μA
I_{CC}	supply current	per input pin; $V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 6.0\text{ V}$	-	-	10	-	20	μA
C_I	input capacitance		-	1.5	-	-	-	pF

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HCT2G00								
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	1.2	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	V
		$I_O = -4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	4.13	4.32	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	0.15	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	± 1.0	-	± 1.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 5.5\text{ V}$	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5\text{ V to }5.5\text{ V}$; $V_I = V_{CC} - 2.1\text{ V}$; $I_O = 0\text{ A}$	-	-	375	-	410	μA
C_I	input capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HC2G00								
t_{pd}	propagation delay	nA and nB to nY; see Figure 6 [1]						
		$V_{CC} = 2.0\text{ V}$	-	25	95	-	110	ns
		$V_{CC} = 4.5\text{ V}$	-	9	19	-	22	ns
		$V_{CC} = 6.0\text{ V}$	-	7	16	-	20	ns
t_t	transition time	see Figure 6 [2]						
		$V_{CC} = 2.0\text{ V}$	-	18	95	-	125	ns
		$V_{CC} = 4.5\text{ V}$	-	6	19	-	25	ns
		$V_{CC} = 6.0\text{ V}$	-	5	16	-	20	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC}$ [3]	-	10	-	-	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25\text{ }^\circ\text{C}$; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HCT2G00								
t_{pd}	propagation delay	nA and nB to nY; see Figure 6	[1]					
		$V_{CC} = 4.5\text{ V}$	-	12	24	-	29	ns
t_t	transition time	$V_{CC} = 4.5\text{ V}$; see Figure 6	[2]					
			-	6	19	-	22	ns
C_{PD}	power dissipation capacitance	$V_1 = \text{GND to } V_{CC} - 1.5\text{ V}$	[3]					
			-	10	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_t is the same as t_{TLH} and t_{THL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms

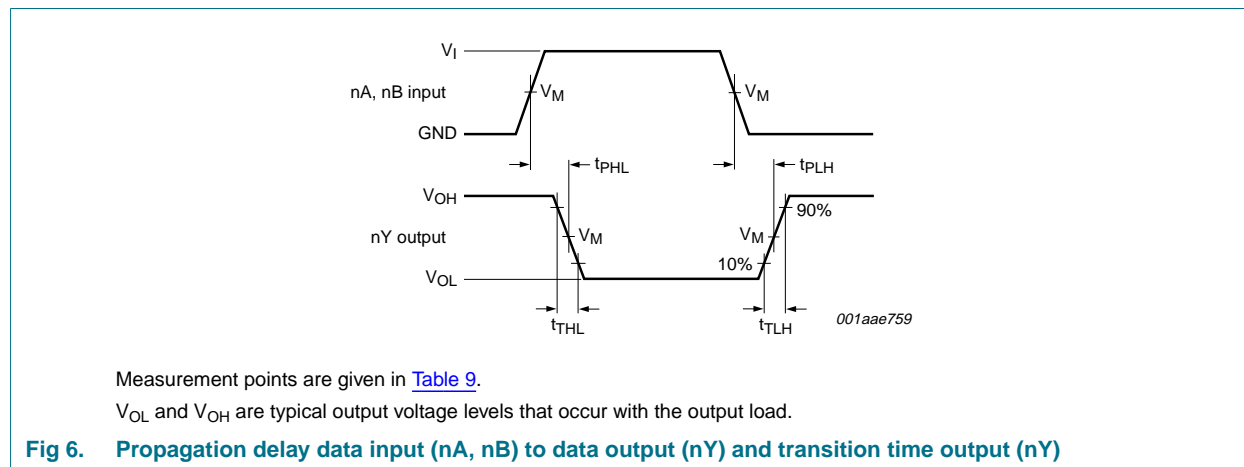


Table 9. Measurement points

Type	Input	Output
	V_M	V_M
74HC2G00	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT2G00	1.3 V	1.3 V

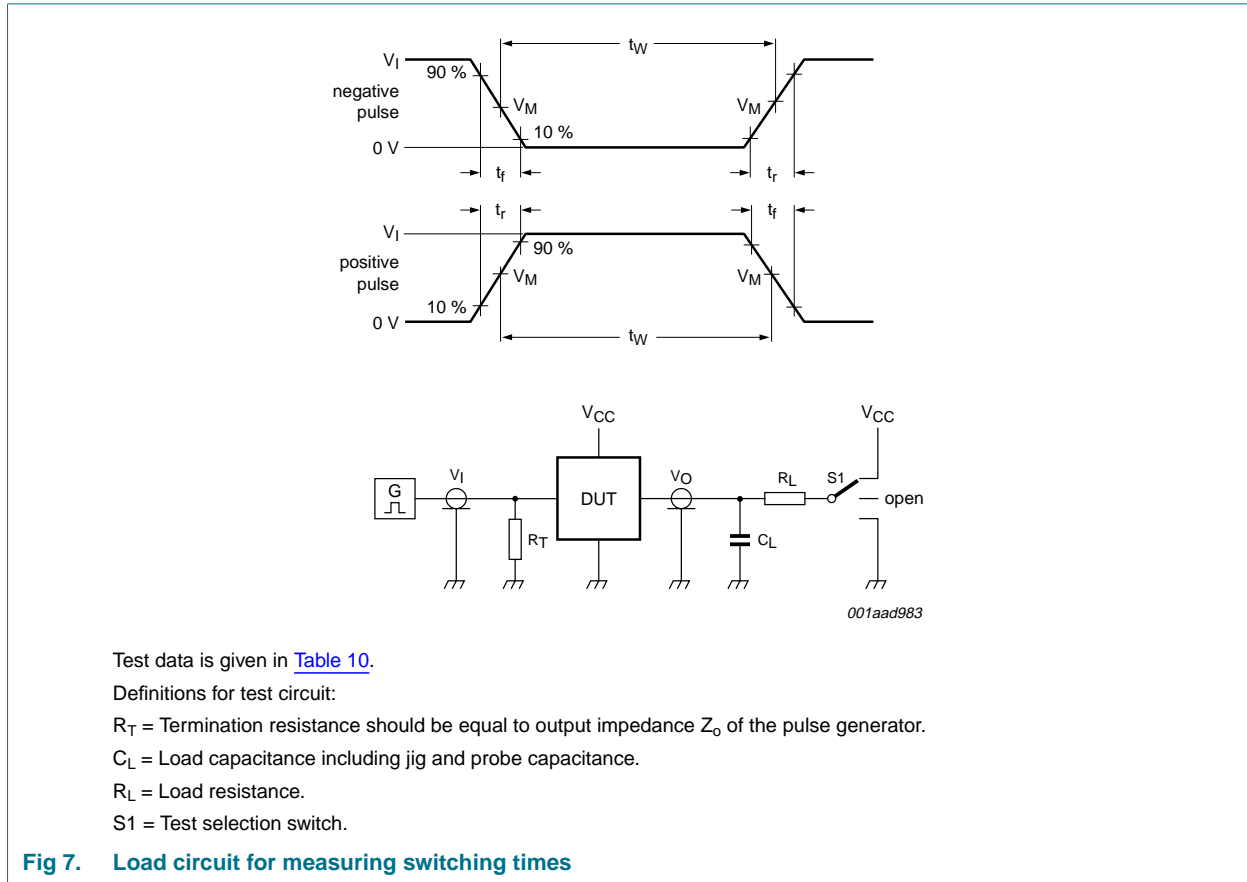


Table 10. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC2G00	V_{CC}	≤ 6 ns	50 pF	1 k Ω	open
74HCT2G00	3 V	≤ 6 ns	50 pF	1 k Ω	open

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

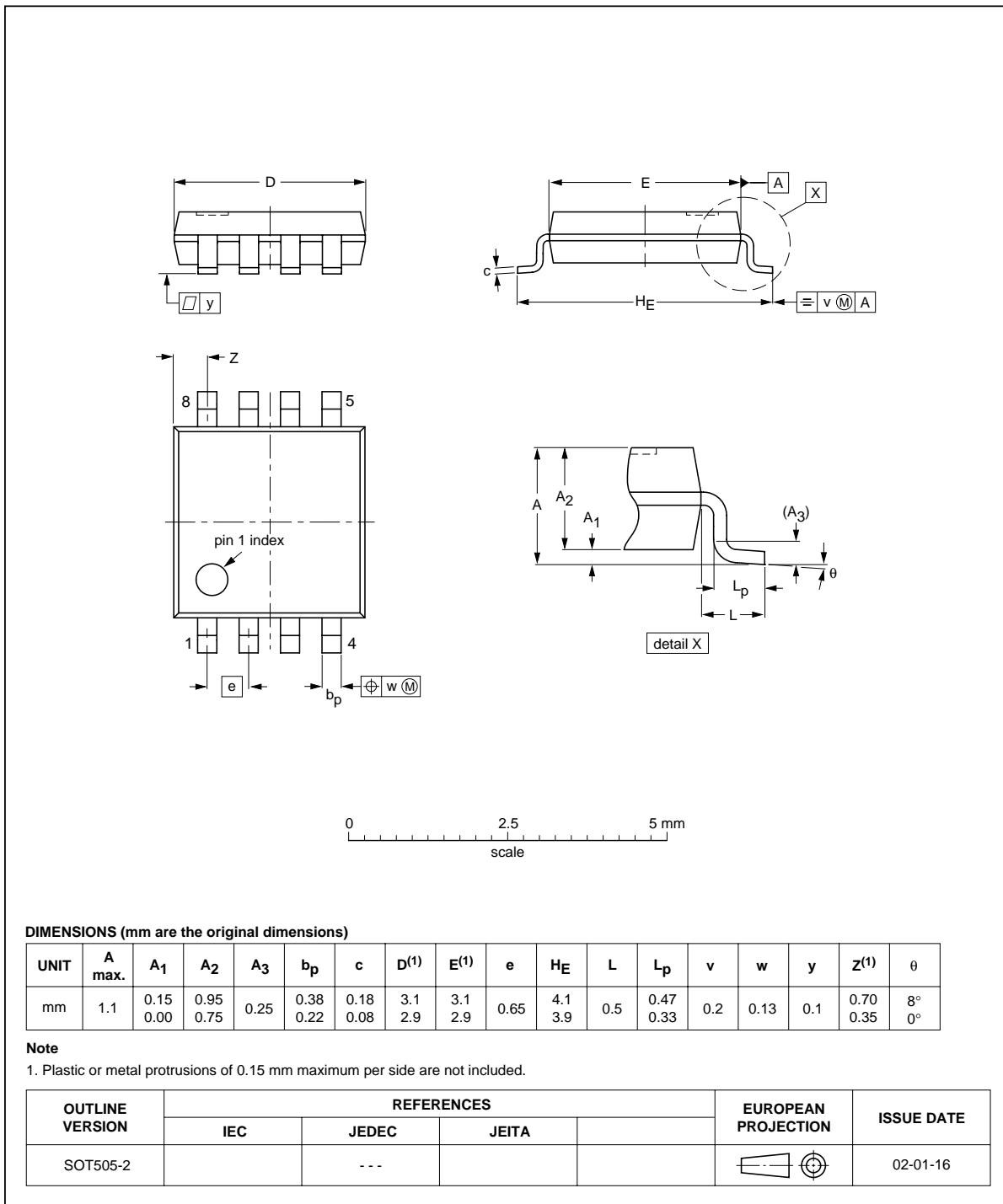


Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

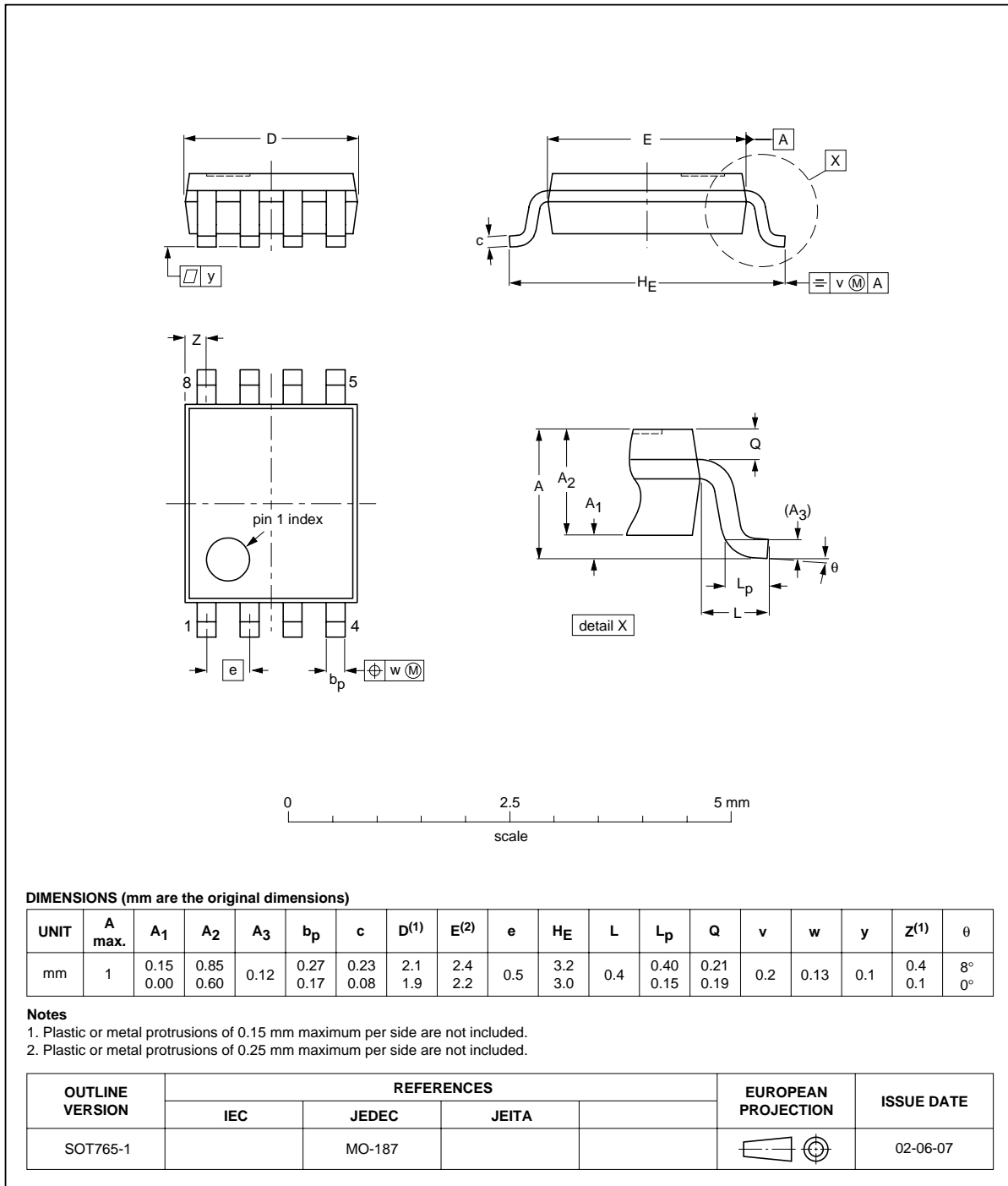


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

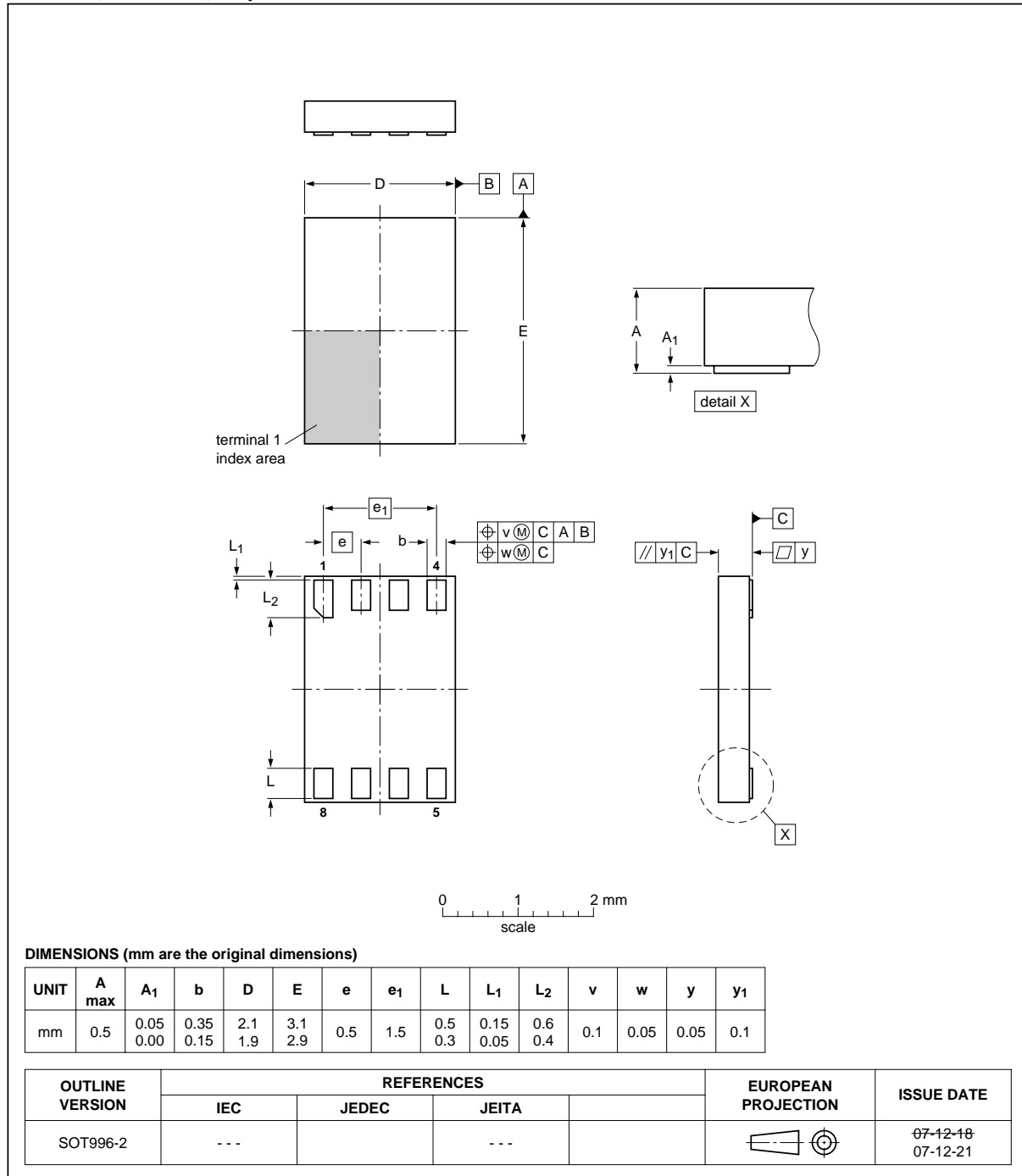


Fig 10. Package outline SOT996-2 (XSON8U)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G00_4	20080703	Product data sheet	-	74HC_HCT2G00_3
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Added type number 74HC2G00GD and 74HCT2G00GD (XSON8U package) 			
74HC_HCT2G00_3	20060405	Product data sheet	-	74HC_HCT2G00_2
74HC_HCT2G00_2	20030212	Product specification	-	74HC_HCT2G00_1
74HC_HCT2G00_1	20020710	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 3 July 2008

Document identifier: 74HC_HCT2G00_4